L Number	Hits	Search Text	DB	Time stamp
2	18	("as.sub.4" or "as.sub.2" or arsenic)	USPAT; US-PGPUB;	2002/07/22 09:45
		same flux	EPO; JPO; DERWENT;	
3	25	117/\$4.ccls. and inas same ratio	IBM_TDB USPAT; US-PGPUB;	2002/07/22
			EPO; JPO; DEPWENT; IBM TDB	03.33
8	30	indium same cell same temperature and 117/\$4.ccls.	USPAT; US-PGPUB; EPO; JPO;	2002/07/22
			DEPWENT; IBM_TDB	
12	51	(inas same substrate same temperature) and 117/\$4.ccls.	USFAT; US-PGPUB; EPO; JPO;	2002/07/22
1.6	2.2		DEPWENT; IBM_TDB	:
16	22	evaporation same temperature same rate same gaas and 117/\$4.ccls.	USFAT; US-PGPUB; EPO; JPO;	2002/07/22 11:44
	4.6	117/01 and and and anti-	DEPWENT; IBM_TDB	2002/07/10
	46	117/\$4.ccls. and gaas and native adj oxide	USPAT: US-PGPUB; EPG; JPO;	13:53
-	19	117/\$4.ccls. and gaas and (desorp\$4 same	DEFWENT; IBM_TNB USPAT;	2002/07/18
		(arsenic or "as.sub.2" or "as.sub.4"))	US-PGFUB; EPG; JPG; DEPWENT;	14:03
-	187	117/\$4.ccls. and super\$llattice and (gaas same substrate) and @py<2001	IBM_TDB USFAT; US-PGFUB;	2002/07/18 14:32
			EPC; JPC; DEPWENT; IBM_TIB	
-	40	117/\$4.ccls. and super\$11attice and (gaas same substrate) and @py-2001 and inas	USFAT; US-PGFUE; EPO; JPO;	2002/07/18 14:35
	2.5	117/01	DEPWENT; IBM_TIB	2002/07/19
	25	117/\$4.ccls. and super\$11attice and (gaas same substrate) and @py<2001 and inas and mbe	USPAT; US-PGPUB; EPO; JPO; DEFWENT;	2002/07/18
- : :	60	(gaas same substrate) and inas and buffer and 117/\$4.ccls.	IBM_TLB USFAT; US-PGFUB;	2002/07/18 15:41
			EPO; JPO; DEPWELT; IBM TDB	i I
- !	83	(arsenic or "as.sub.2" or "as.sub.4") and adjust\$3 same thickness and 117/\$4.ccls.	USFAT; US-PGFUB; EPO; JPO;	2002/07/19 10:23
;			DEFWENT; IBM_TIB	2002 07/16
_	48	(arsenic or "as.sub.2" or "as.sub.4") and adjust\$3 same thickness same temperature and 117/\$4.ccls.	USFAT; US-PGFUB; EPC; JPC;	2002/07/19 10:29
	· · · · · · · · · · · · · · · · · · ·	<u> </u>	DERWENT; IBM_TLB	·

-	150		USPAT;	2002/07/19
		and gaas	US-PGPUB;	10:30
			EPO; JPO;	
			DERWENT;	!
			IBM TDB	
-	63	117/\$4.ccls. and amorphous same anneal\$3	USPAT;	2002/07/19
		and gaas	US-PGPUB;	10:32
	į		EPO; JPO;	
1			DERWENT;	
			IBM TDB	
-	5 4	117/\$4.ccls. and (ga or gallium) same	USPAT;	2002/07/19
		cell same temperature and mbe	US-PGPUB;	13:22
			EPO; JPO;	13.22
ŀ			DERWENT;	
			IBM TDB	
_	44	117/\$4.ccls. and gaas same buffer and	USFAT;	2002/07/19
		inas	US-PGPUB;	13:29
			1	1 23.23
			EPO; JPO;	
			DEPWENT;	
	1.0	117/64	IBM_TDB	2002/07/10
_	12	117/\$4.ccls. and evaporate same	USPAT;	2002/07/19
		temperature same arsenic	US-PGPUB;	13:50
			EPO; JPO;	
			DEPWENT;	
		/	IBM_TDB	
-	63	117/\$4.ccls. and evaporat\$3 same	USFAT:	2002/07/19
		temperature same arsenic	US-PGPUB;	13:50
l I		1	EPO; JPO;	
			DEPWENT;	
			IBM_TDB	
~	186		USFAT:	2002/07/19
<u> </u>		amorphous and gaas	US-PGPUB;	15:31
			EPO; JPO;	
: 			DEFWENT;	
			IBM_TDB	į į
- !	57	117/\$4.ccls. and single adj crystal same	USFAT;	2002/07/19
		amorphous same gaas	US-PGPUB;	16:11
!			EPO; JPO;	
			DEPWENT;	<u>'</u>
			IBM_TDB	
-	190	117/\$4.ccls. and low adj temperature same	USPAT;	2002/07/19
		gaas	US-PGPUB;	16:17
			EPO; JPO;	1
			DEFWENT;	
			IBM TDB	
_	30	117/\$4.ccls. and low adj temperature same	USFAT;	2002/07/19
		gaas same pressure	US-PGPUB;	16:14
			EPO; JPO;	
			DEFWENT;	:
			IBM TDB	:
_	165	117/\$4.ccls. and gaas same pressure and	USPAT;	2002/07/22
	100	mbe	US-PGPUB;	09:39
;			EPO; JPO;	
:			DEFWENT;	
			IBM TDB	